ALPHA & OMEGA SEMICONDUCTOR

AON6403

30V P-Channel MOSFET

General Description

The AON6403 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

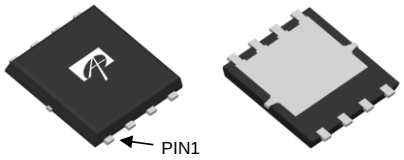
Product Summary

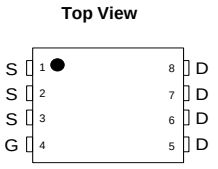
V_{DS}	-30V
I_D (at V_{GS}= -10V)	-85A
$R_{DS(ON)}$ (at V_{GS}= -10V)	< 3.1mΩ
$R_{DS(ON)}$ (at V_{GS} = -4.5V)	< 4.3mΩ

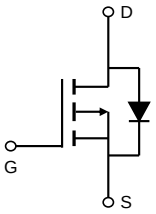
100% UIS Tested
100% R_g Tested

Green Product

DFN5X6







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	**-30**	V
Gate-Source Voltage		V_{GS}	**±20**	V
Continuous Drain Current [G]	T_C=25°C	I_D	**-85**	A
	T_C=100°C		**-67**	
Pulsed Drain Current [C]		I_{DM}	**-280**	
Continuous Drain Current	T_A=25°C	I_{DSM}	**-21**	A
	T_A=70°C		**-17**	
Avalanche Current [C]		I_{AR}	**-72**	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	**259**	mJ
Power Dissipation [B]	T_C=25°C	P_D	**83**	W
	T_C=100°C		**33**	
Power Dissipation [A]	T_A=25°C	P_{DSM}	**2.3**	W
	T_A=70°C		**1.4**	
Junction and Storage Temperature Range		T_J, T_{STG}	**-55 to 150**	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	14	17	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		40	55	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1	1.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-1.2	-1.7	-2.2	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V	-280			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-20A		2.6	3.1	mΩ
		T_J=125°C		3.6	4.4	
		V_{GS}=-4.5V, I_D=-20A		3.5	4.3	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-20A		82		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-85	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz	6100	7600	9120	pF
C_{oss}	Output Capacitance		930	1320	1720	pF
C_{rss}	Reverse Transfer Capacitance		630	1050	1470	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	1	2	4	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-20A	130	163	196	nC
Q_g(4.5V)	Total Gate Charge		63	79	95	nC
Q_{gs}	Gate Source Charge		18	22	26	nC
Q_{gd}	Gate Drain Charge		20	33	46	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=0.75Ω, R_{GEN}=3Ω		13		ns
t_r	Turn-On Rise Time			18		ns
$t_{D(off)}$	Turn-Off DelayTime			135		ns
t_f	Turn-Off Fall Time			52		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-20A, dI/dt=500A/µs	21	26	32	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-20A, dI/dt=500A/µs	63	78	94	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.Maximum UIS current limited by test equipment.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by package.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

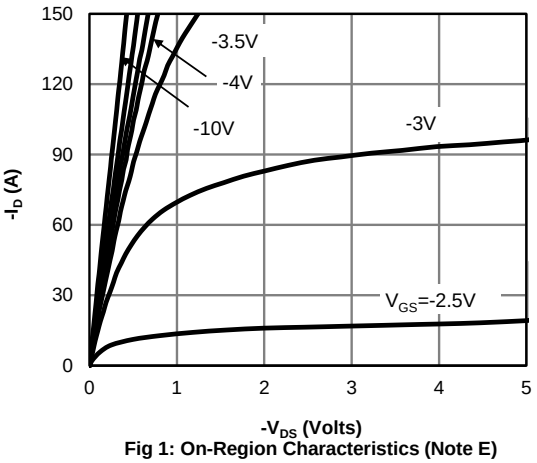


Fig 1: On-Region Characteristics (Note E)

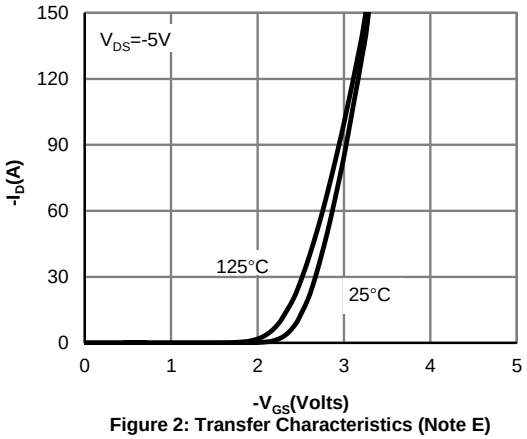


Figure 2: Transfer Characteristics (Note E)

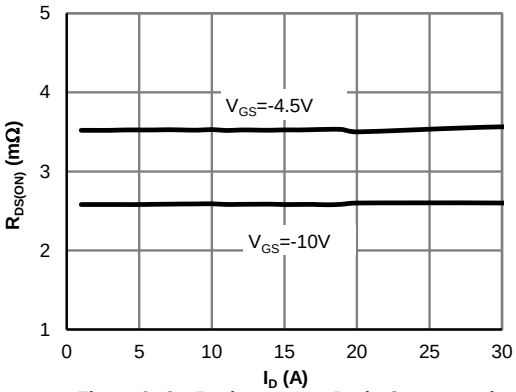


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

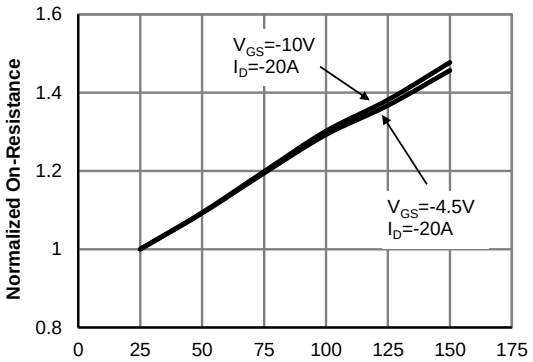


Figure 4: On-Resistance vs. Junction Temperature (Note E)

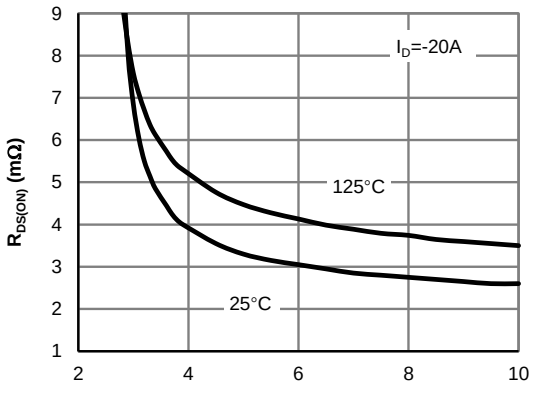


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

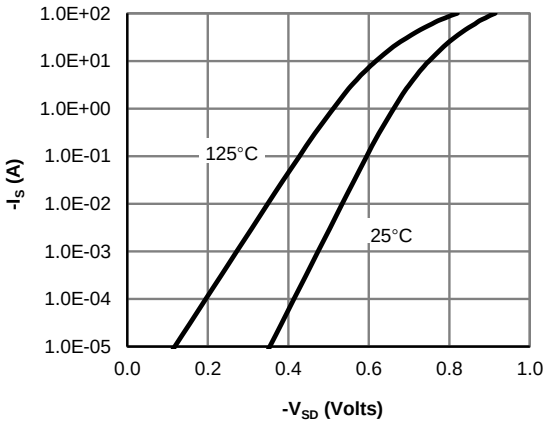


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

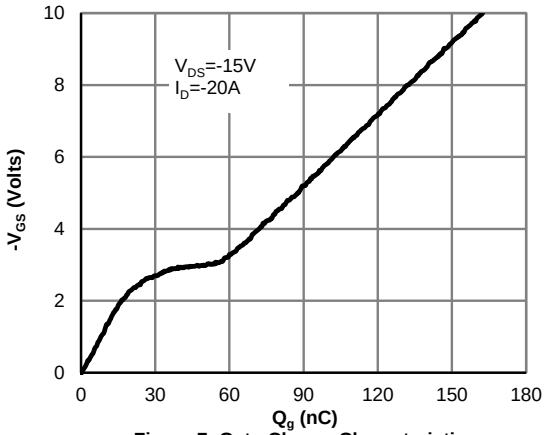


Figure 7: Gate-Charge Characteristics

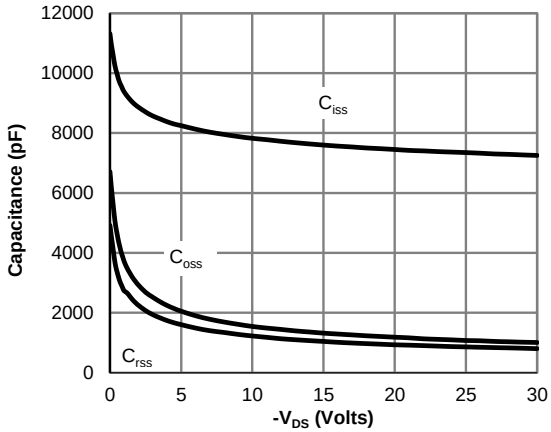


Figure 8: Capacitance Characteristics

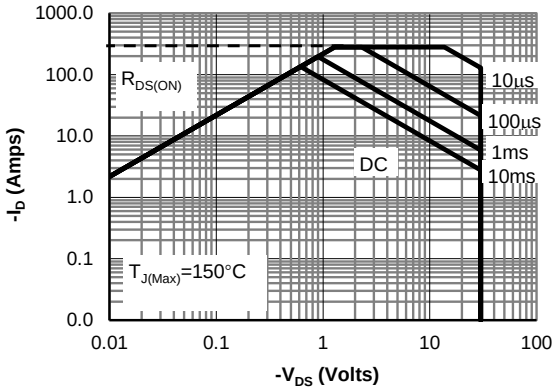


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

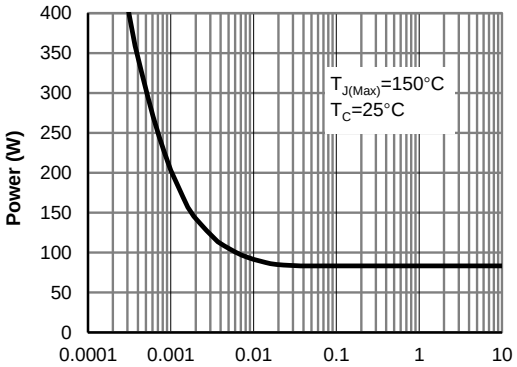


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

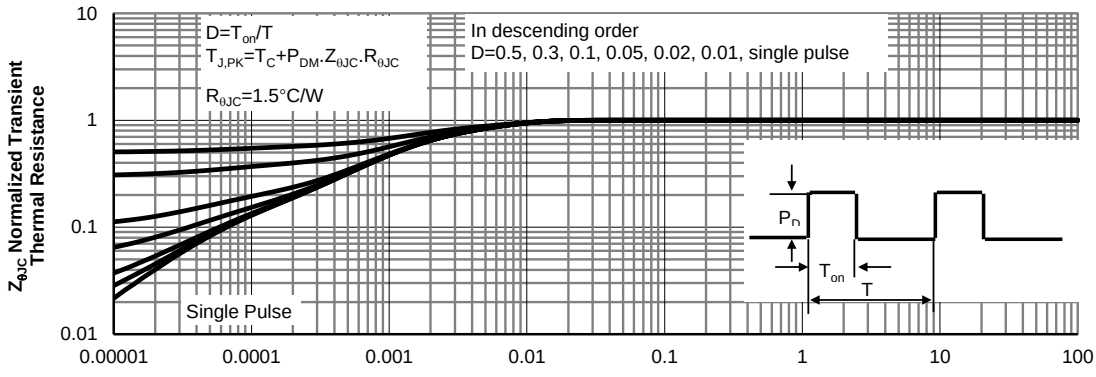


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

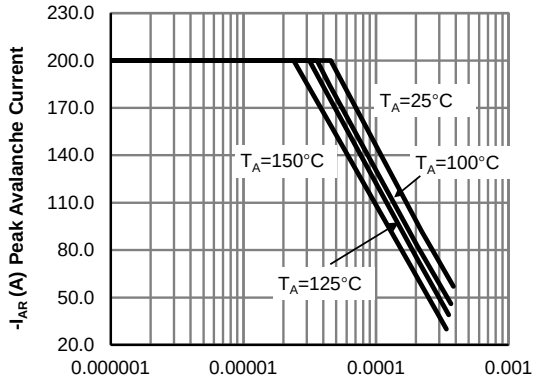


Figure 12: Single Pulse Avalanche capability (Note C)

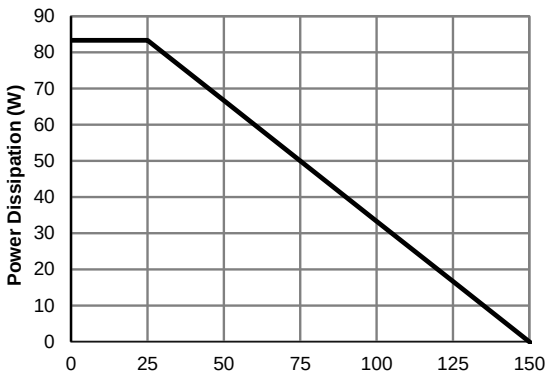


Figure 13: Power De-rating (Note F)

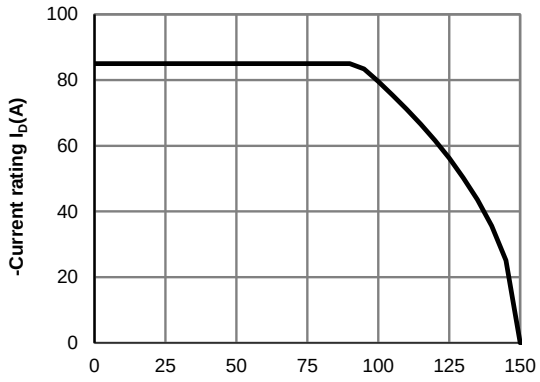


Figure 14: Current De-rating (Note F)

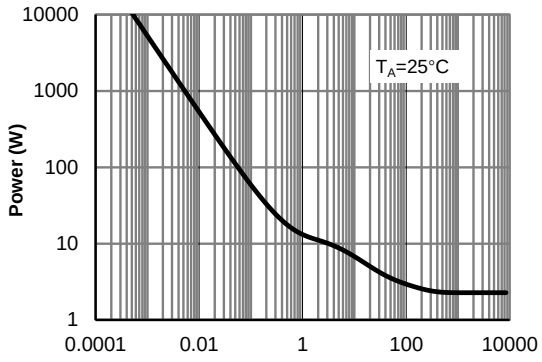


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

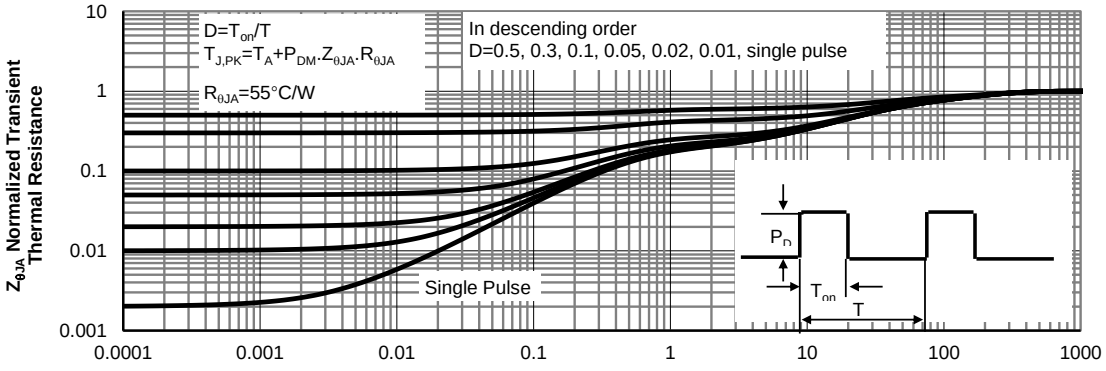
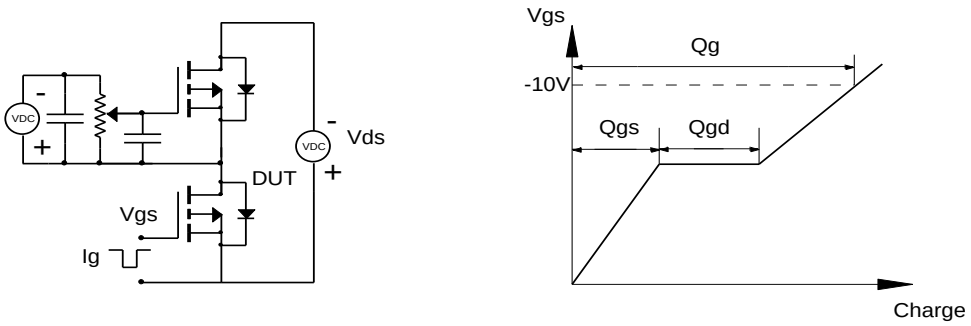
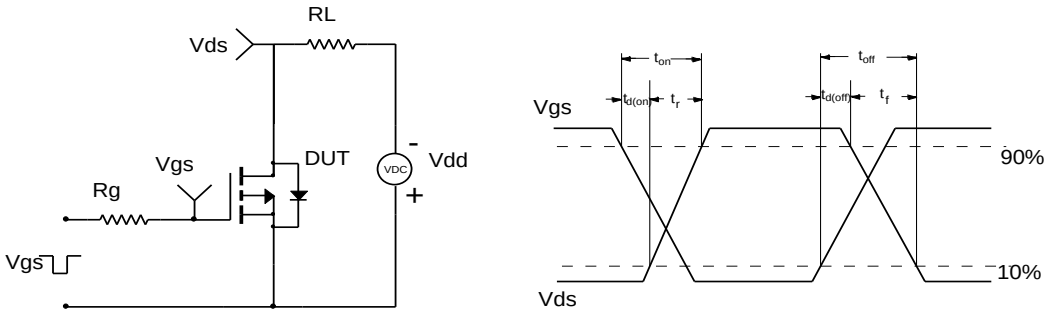


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

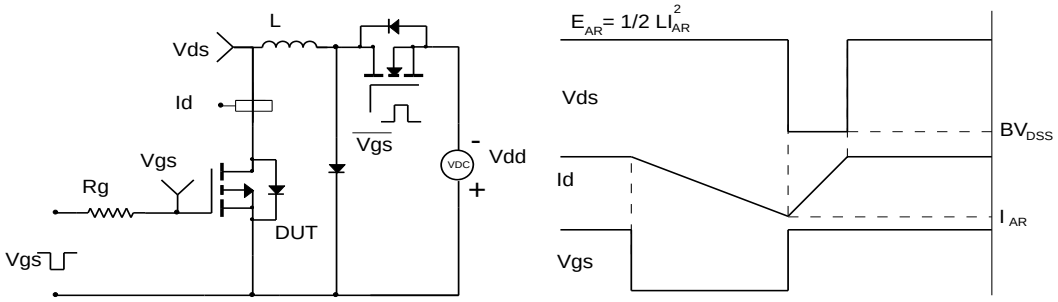
Gate Charge Test Circuit & Waveform



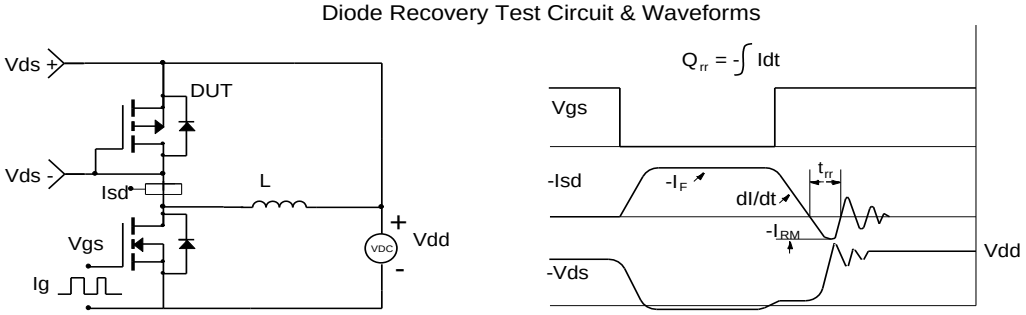
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